YJG310G04HJRQ

RECOMMEND
YJG300G04HRQ
FOR NEW DESIGN

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	40V
I_D	310A
$R_{DS(ON)}$(at V_{GS}=10V)	0.95m
100% EAS Tested	
100% V_{DS} Tested	

General Description

Excellent package for heat dissipation

a91 g0 0 596.04 842.04596.04 842.04 reW4 nBT/TT0 9 Tf315.67 640.9 Td( )TjETEMC

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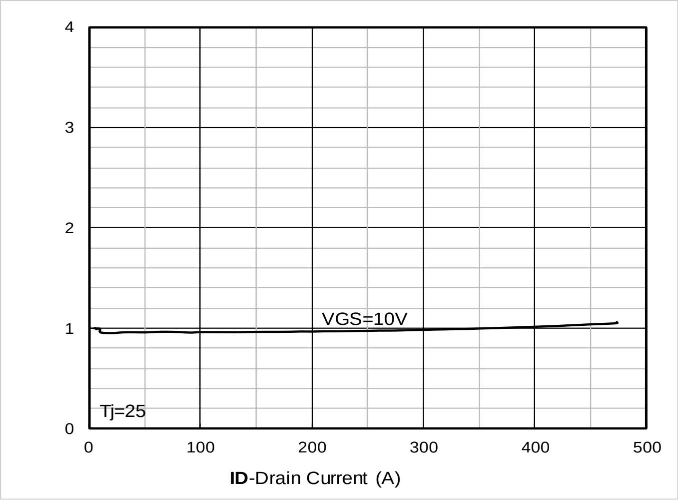


Figure 7. RDS(on) VS Drain Current

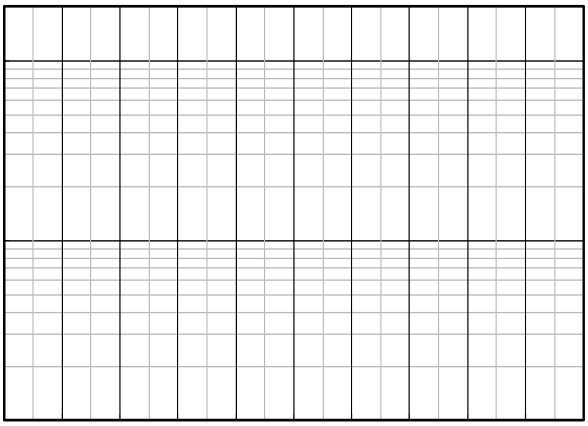


Figure 8. Forward characteristics of reverse diode

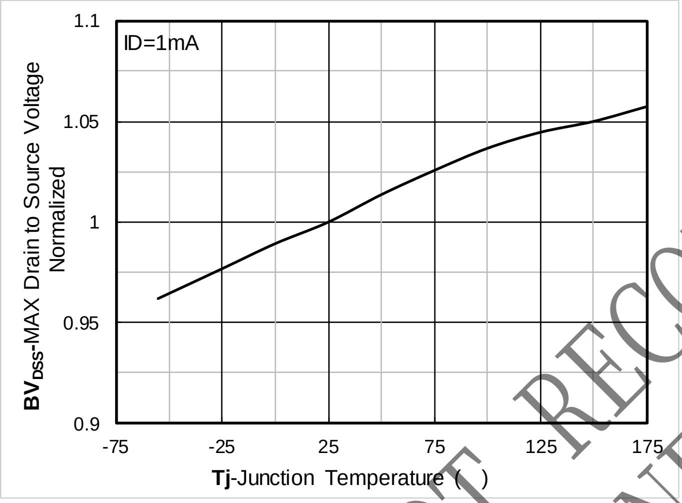


Figure 9. Normalized breakdown voltage

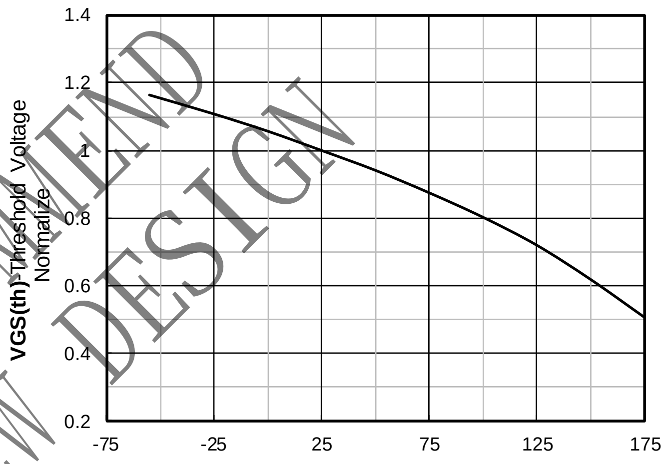


Figure 10. Normalized Threshold voltage

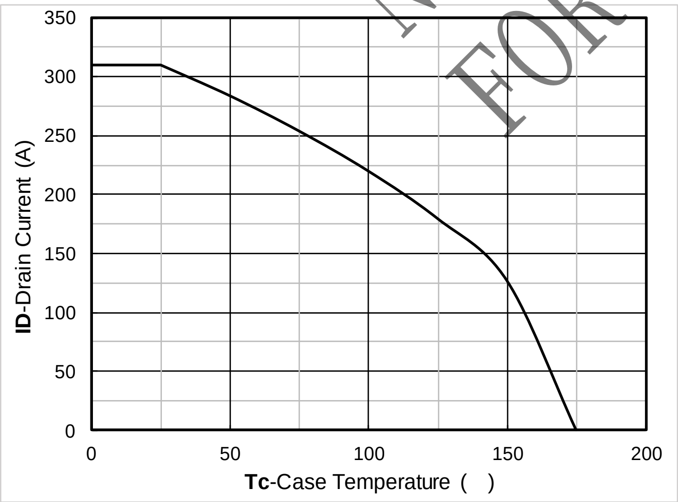


Figure 11. Current dissipation

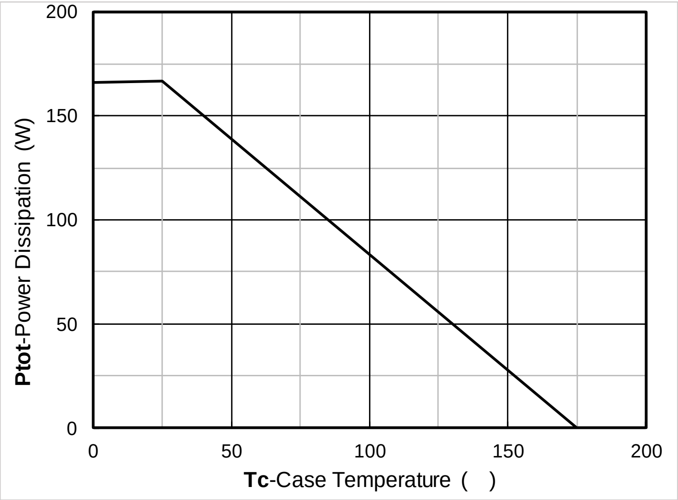


Figure 12. Power dissipation

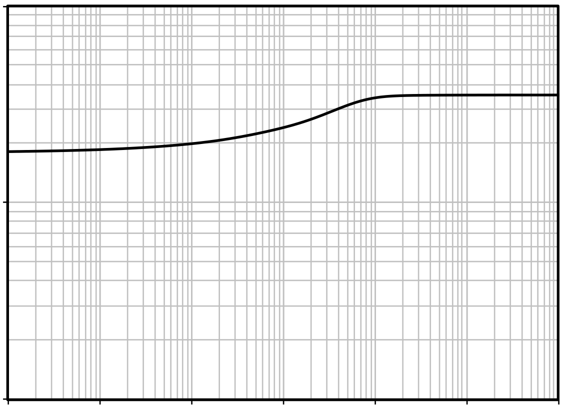
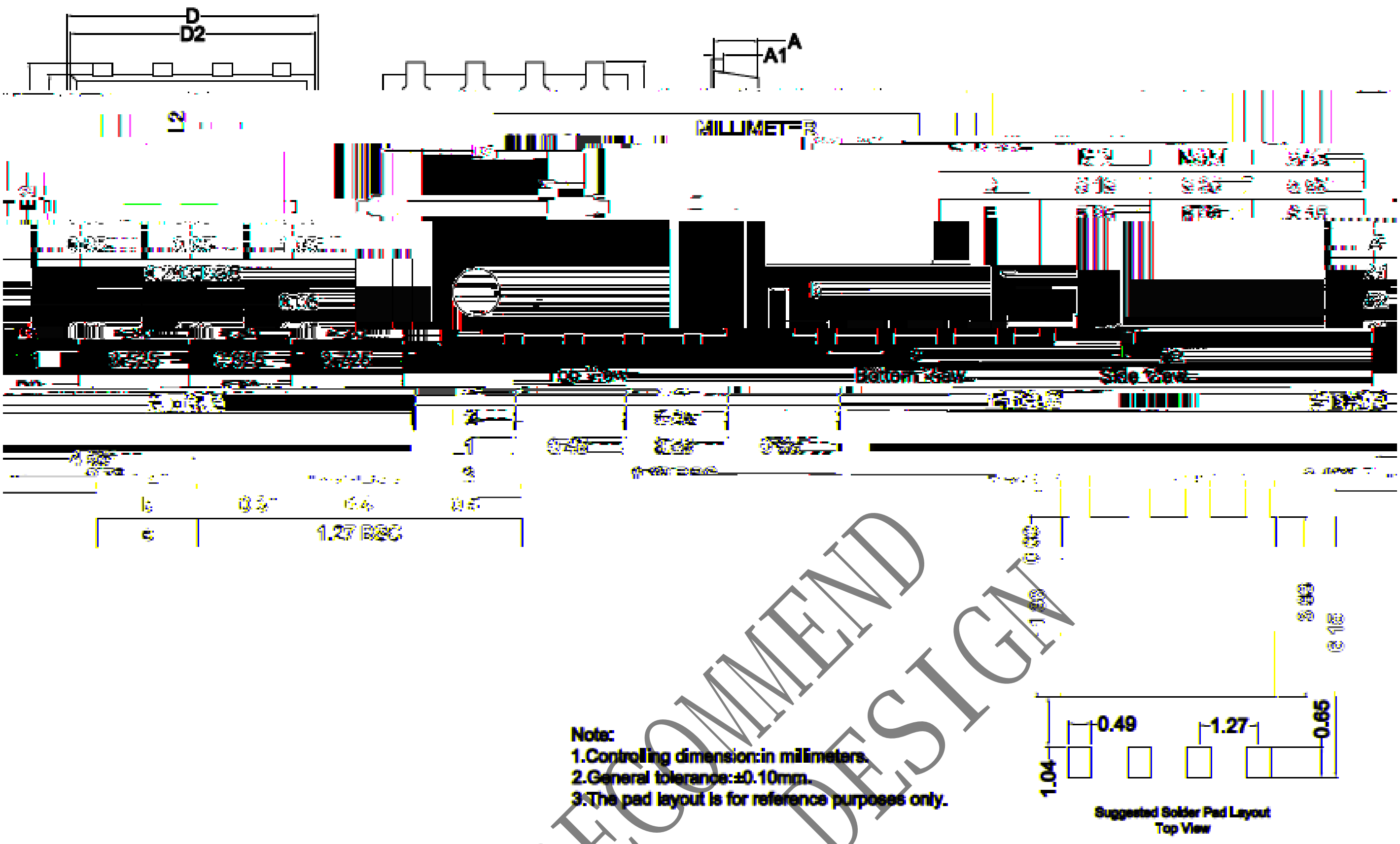


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

PDFN5060-8L-0.95MM Package information



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.10mm.
3.The pad layout is for reference purposes only.

Disclaimer